

General Description

The CMSA085N06 uses advanced technology to provide excellent RDS (ON), low gate charge and minimize the loss of power conversion applications. This device is suitable to be used as the low side FET in SMPS, load switching and general purpose.

Features

- Low On-Resistance
- 100% avalanche tested
- Simple Drive Requirements
- RoHS Compliant

Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	60	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D@T_C=25^\circ\text{C}$	Continuous Drain Current	50	A
$I_D@T_C=100^\circ\text{C}$	Continuous Drain Current	35	A
I_{DM}	Pulsed Drain Current	200	A
EAS	Single Pulse Avalanche Energy ¹	56	mJ
$P_D@T_C=25^\circ\text{C}$	Total Power Dissipation	50	W
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ\text{C}$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ\text{C}$

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient($t \leq 10\text{s}$)	---	20	$^\circ\text{C/W}$
$R_{\theta JC}$	Thermal Resistance Junction -Case(Steady State)	---	2.4	$^\circ\text{C/W}$

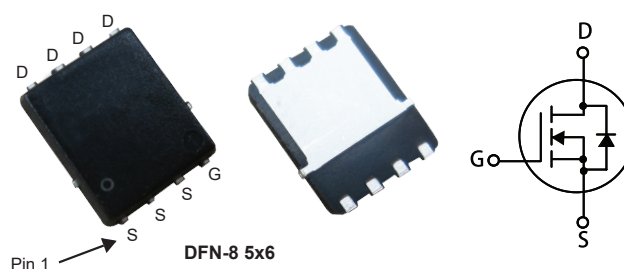
Product Summary

BVDSS	RDS(ON)	ID
60V	9.1m Ω	50A

Applications

- Synchronous Rectification in SMPS
- ATX and Gaming Power Supplies
- Switching Applications

DFN-8 5x6 Pin Configuration



Type	Package	Marking
CMSA085N06	DFN-8 5*6	CMSA085N06

N-Channel Enhancement Mode Field Effect Transistor

Electrical Characteristics ($T_J=25^{\circ}\text{C}$, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V$, $I_D=250\mu A$	60	---	---	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance	$V_{GS}=10V$, $I_D=20A$	---	7.8	9.1	$m\Omega$
		$V_{GS}=4.5V$, $I_D=10A$	---	12	13	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}$, $I_D=250\mu A$	1.0	---	2.5	V
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=60V$, $V_{GS}=0V$	---	---	1	μA
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 20V$, $V_{DS}=0V$	---	---	± 100	nA
g_{fs}	Forward Transconductance	$V_{DS}=10V$, $I_D=20A$	---	16	---	S
Q_g	Total Gate Charge	$V_{DS}=30V$, $I_D=10A$ $V_{GS}=4.5V$	---	10	---	nC
Q_{gs}	Gate-Source Charge		---	4	---	
Q_{gd}	Gate-Drain Charge		---	2	---	
$T_{d(on)}$	Turn-On Delay Time	$V_{DS}=30V$, $V_{GS}=10V$, $R_L=3\Omega$ $R_{GEN}=1\Omega$, $I_D=10A$	---	25	---	ns
T_r	Rise Time		---	110	---	
$T_{d(off)}$	Turn-Off Delay Time		---	15	---	
T_f	Fall Time		---	7	---	
C_{iss}	Input Capacitance	$V_{DS}=25V$, $V_{GS}=0V$, $f=1MHz$	---	1300	---	pF
C_{oss}	Output Capacitance		---	550	---	
C_{rss}	Reverse Transfer Capacitance		---	35	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Diode continuous forward current	$V_G=V_D=0V$, Force Current	---	---	50	A
I_{SM}	Pulsed Source Current		---	---	200	A
V_{SD}	Diode Forward Voltage	$V_{GS}=0V$, $I_S=28A$, $T_J=25^{\circ}\text{C}$	---	0.86	1.2	V

Notes:

1. The EAS data shows Max. rating .The test condition is $V_{DS}=30V$, $V_{GS}=10V$, $L=0.5mH$, $I_{AS}=15A$.

This product has been designed and qualified for the consumer market.

Cmos assumes no liability for customers' product design or applications.

Cmos reserves the right to improve product design ,functions and reliability without notice.

N-Channel Enhancement Mode Field Effect Transistor

Typical Characteristics

